

ME 412: Active components

- powered devices that change behavior when powered.

- A key example: the transistor:
name is concatenation of

"[Transfer Resistor]"

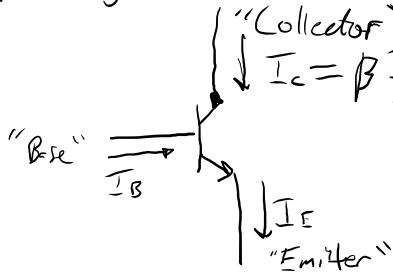
- A type of controlled resistor.

Transistors function like valves: modulate current with an input.

Transistors are 3-pole devices:

bipolar junction transistor (BJT):

npn:



$$I_C = \beta I_B$$

β is typ. large, > 100 .

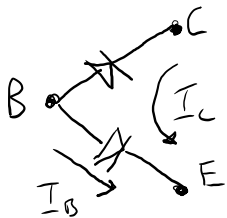
$$I_E = I_C + I_B$$

Rules of transistors: 2 types npn, pnp.

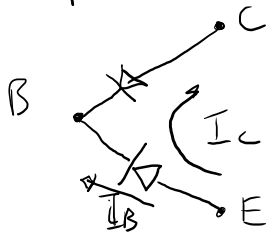
(reverse the polarities of above rules for pnp-type).

1. Collector must be "more positive" than the emitter
2. Base-Emitter & Base-Collector junctions behave like diodes:

n pn



pnp



* Diodes are non-linear passive devices : AOE p. 44.

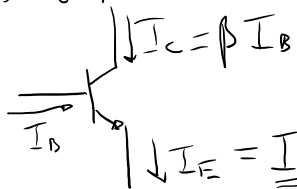
3. Any transistor has a maximal I_C , I_B , V_{CE} . IF these values are exceeded, the device is destroyed.

"proportional to"

4. $I_C \sim I_B$, where $I_C = h_{FE} I_B = \beta I_B$
 β typ. > 100 . * β is typically not a precise value, even for same part #'s

• No design should rely on β 's value

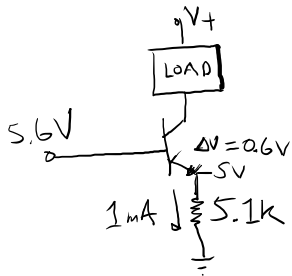
Re-state rule #41: Small base currents \rightarrow large collector currents.



$$I_E = \underline{I_C} + \underline{I_B} = (1 + \beta) I_B \approx I_C.$$

Devices w/ transistor:

* CURRENT SOURCE:



Ohm's law:

$$V = IR$$

$$\Rightarrow I_E = \frac{5V}{5k\Omega} = 1mA.$$

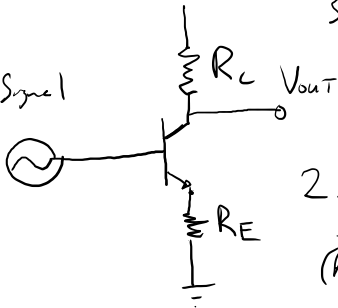
Thought Experiment: Suppose $V_+ = 20V$, load is variable resistor $50k\Omega$. (trim pot).

- What happens as we vary the value of R_{load} from 0 to $50k\Omega$?
- Does the behavior deviate from "Ideal current source" or not?

Ideal behavior breaks when $R_{load} > \frac{14V}{1mA} \approx 14k\Omega$.

* EMITTER AMPLIFIER:

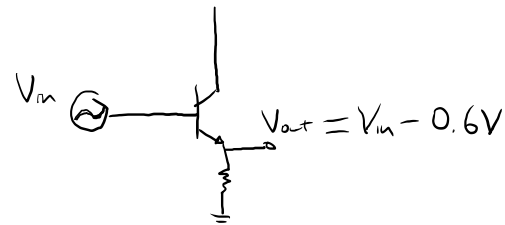
1. Apply Signal ΔV_B



3. $\Delta I_C \rightsquigarrow \Delta V_{OUT}$
(lg. $R_C \rightsquigarrow$ lg. ΔV_{OUT})

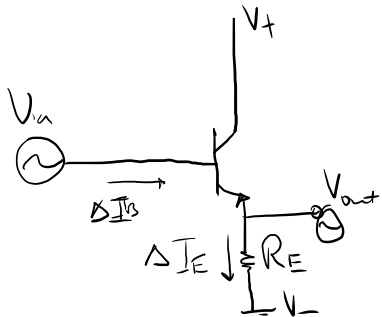
2. $\Delta V_B \rightsquigarrow \Delta V_E$;
 $\Rightarrow \Delta I_E$: Small $R_E \Rightarrow$ lg. ΔI_E
(Recall Ohm: $\Delta I_E = \frac{\Delta V_E}{R_E}$)

* Emitter-Follower:



Why do we use this?
"Rose-colored lens" effect

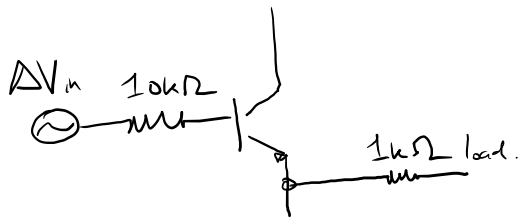
A closer look at the Emitter-Follower:



1. ΔV_{in} , ΔV_{out} are the same

2. ΔI_B , ΔI_E are very different.

Generalized Ohm: $\frac{\Delta V}{\Delta I} = Z$



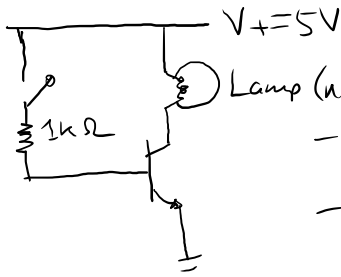
1. "Looking into" transistor from output side: Load "sees" ΔI_E from ΔV_{in}

$$R_{eff} = \frac{\Delta V_{in}}{\Delta I_E} = \frac{\Delta V_{in}}{\beta \Delta I_B} \approx \frac{R_B}{100}$$

2. Looking into the transistor from the base:
base "sees" the $1k\Omega$ load as:

$$R_{in} = \frac{\Delta V_E}{\Delta I_B} = \frac{\beta \Delta V_E}{\Delta I_E} = \beta R_{LOAD} \approx 100 R_{LOAD}$$

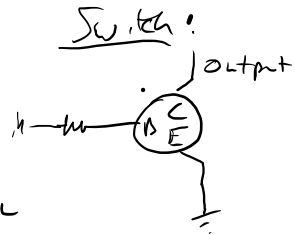
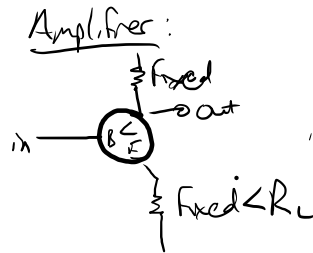
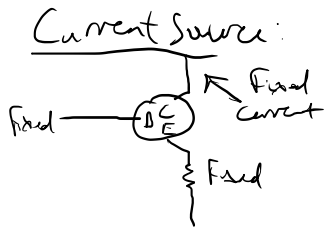
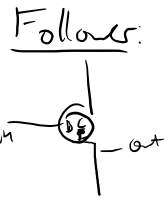
A Different transistor device: The switch. (How computers & logic work)



$V_+ = 5V$
Lamp (non-linear resistor)

* Binary response:
on or off.

- purposely over-driven, $10 \times I_{c}$ to obtain reg'd I_c
- V_{CE} is kept low. (All power goes thru lamp).



AOE ps 98-102 ; Ebers-Moll: § 2.10 & 2.11.

All labwork today: BJT,
FET. (More common).

Lab exercises